DXT3904

40V NPN SMALL SIGNAL TRANSISTOR IN SOT89

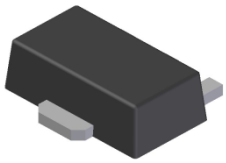
Features

- BV_{CEO} > 40V
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT3906)
- Ideal for Medium Power Switching or Amplification Applications
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

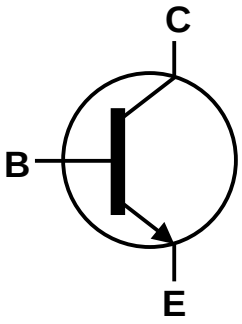
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

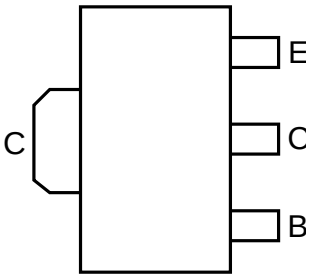
SOT89



Top View



Device Symbol



Top View
Pin-Out

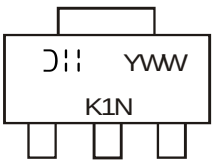
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT3904-13	AEC-Q101	K1N	13	12	2,500

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free,"Green" and Lead-Free.
3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

(Top View)



K1N = Product Type Marking Code
YWW = Date Code Marking
Y = Last Digit of Year ex: 4 = 2014
WW = Week Code 01 - 52

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current – Continuous	I_C	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	0.75	W
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	166	°C/W
	(Note 6)		104	
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the exposed collector pad on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	V	I_C = 10μA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
Base Cutoff Current	I_{BL}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h_{FE}	40 70 100 60 30	— — 300 — —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 50mA, V_{CE} = 1.0V I_C = 100mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.20 0.30	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65 —	0.85 0.95	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	10	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.5	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 10mA, f = 100MHz
Noise Figure	NF	—	5.0	dB	V_{CE} = 5.0V, I_C = 100μA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = 3.0V, I_C = 10mA, $V_{BE(off)}$ = -0.5V, I_{B1} = 1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	200	ns	V_{CC} = 3.0V, I_C = 10mA, I_{B1} = -I_{B2} = 1.0mA
Fall Time	t_f	—	50	ns	

Notes: 7. Measured under pulsed condition. Pulse width = 300μs. Duty cycle ≤2%.

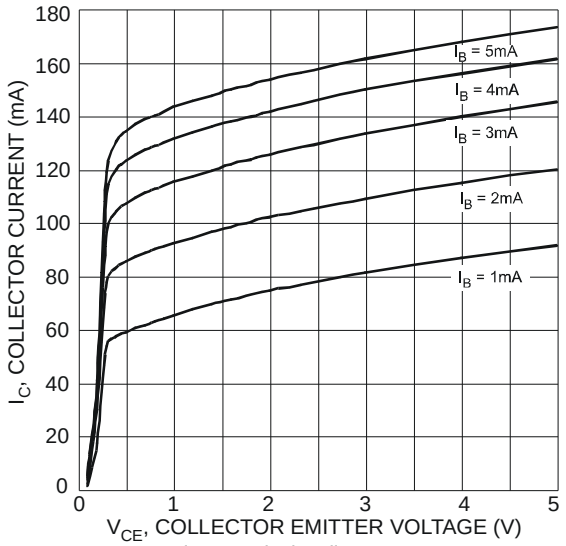


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

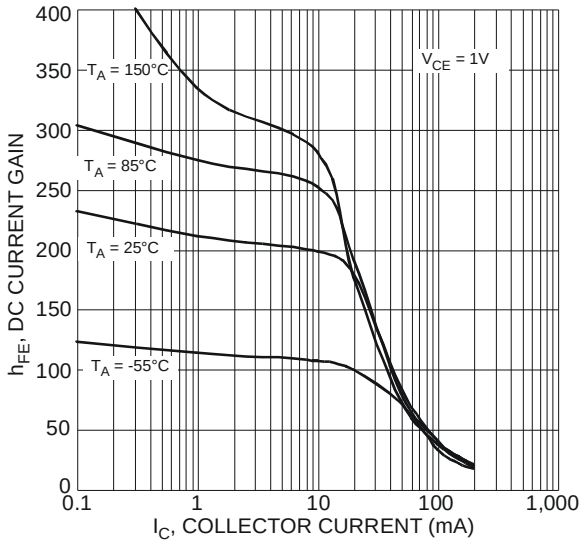


Fig. 3 Typical DC Current Gain vs. Collector Current

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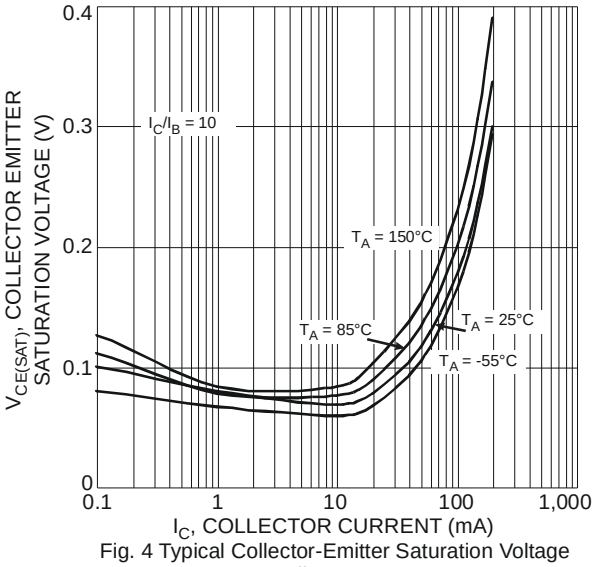


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

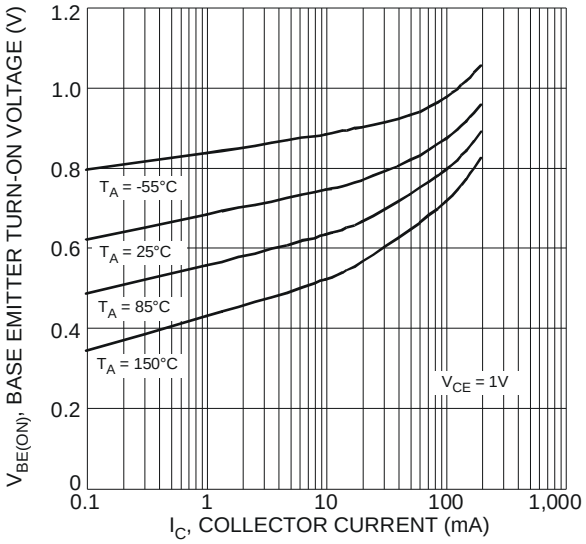


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

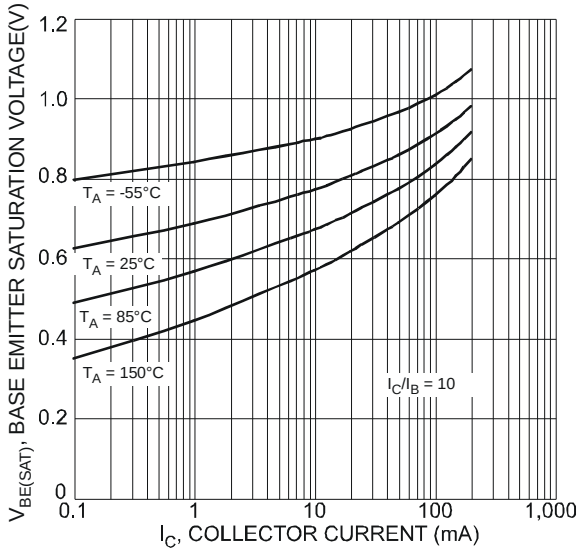


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

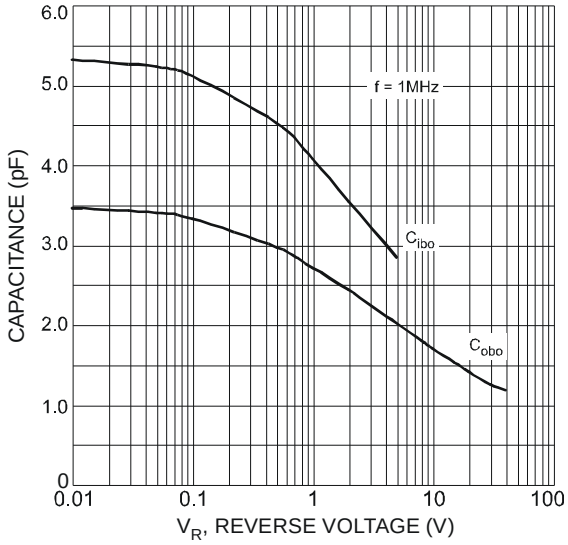


Fig. 7 Typical Capacitance Characteristics

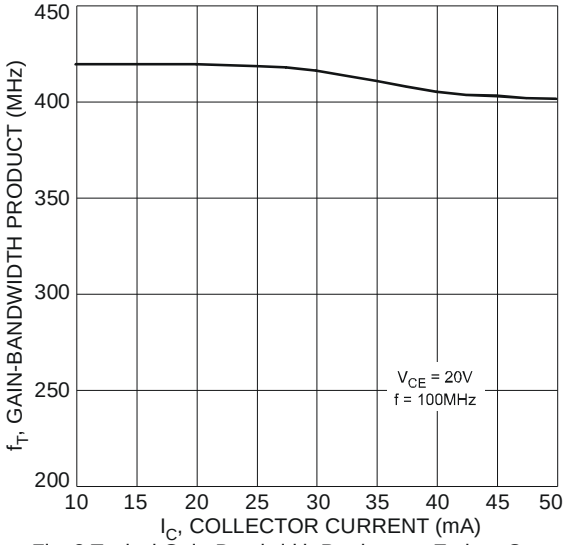
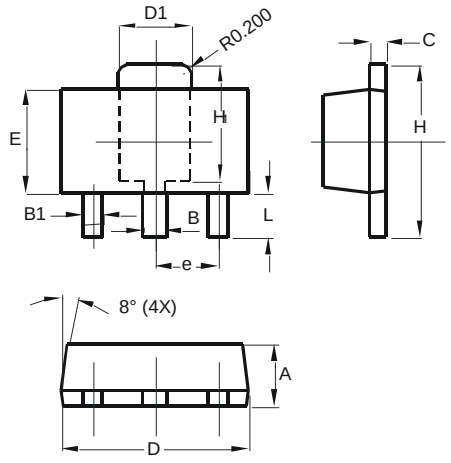


Fig. 8 Typical Gain-Bandwidth Product vs. Emitter Current

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Package Outline Dimensions

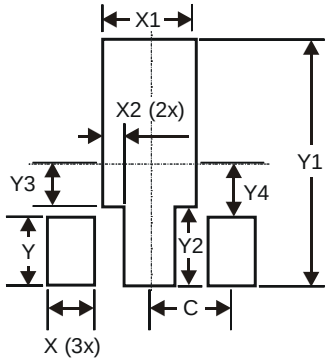
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT89		
Dim	**Min**	**Max**
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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